

MBR735, MBR745

SWITCHMODE™ Power Rectifiers

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- Pb-Free Packages are Available*

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

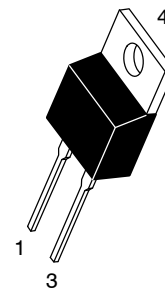
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B
Machine Model C

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

SCHOTTKY BARRIER RECTIFIERS 7.5 AMPERES 35 and 45 VOLTS



TO-220AC
CASE 221B
PLASTIC
STYLE 2

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
B7x5 = Device Code
x = 3 or 4
KA = Diode A Polarity
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MBR735	TO-220	50 Units/Rail
MBR735G	TO-220 (Pb-Free)	50 Units/Rail
MBR745	TO-220	50 Units/Rail
MBR745G	TO-220 (Pb-Free)	50 Units/Rail

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35 45	V
Average Rectified Forward Current ($T_C = 164^\circ\text{C}$)	$I_{F(AV)}$	7.5	A
Peak Repetitive Forward Current, (Square Wave, 20 kHz, $T_C = 168^\circ\text{C}$)	I_{FRM}	7.5	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	1.0	A
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	T_J	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	$^\circ\text{C}/\text{W}$
Maximum Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

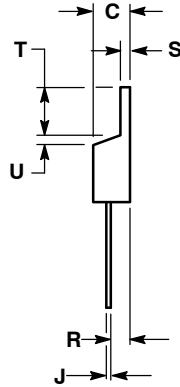
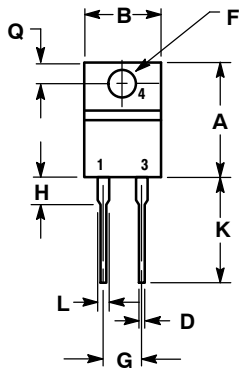
Characteristic	Symbol	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 7.5$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 15$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 15$ Amps, $T_J = 25^\circ\text{C}$)	V_F	-	0.48 0.61 0.68	0.57 0.72 0.84	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	-	10 0.03	15 0.1	mA

- Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

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PACKAGE DIMENSIONS

TO-220
 PLASTIC
 CASE 221B-04
 ISSUE E



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

- STYLE 2:
 PIN 1. ANODE
 2. N/A
 3. CATHODE
 4. ANODE